

# BC847/BC547 series

45 V, 100 mA NPN general-purpose transistors

Rev. 07 — 10 December 2008

Product data sheet

## 1. Product profile

### 1.1 General description

NPN general-purpose transistors in small plastic packages.

Table 1. Product overview

Type number <sup>[1]</sup>	Package			PNP complement
	NXP	JEITA	JEDEC	
BC847	SOT23	-	TO-236AB	BC857
BC847A				BC857A
BC847B				BC857B
BC847B/DG				-
BC847C				BC857C
BC847W	SOT323	SC-70	-	BC857W
BC847AW				BC857AW
BC847BW				BC857BW
BC847BW/DG				-
BC847CW				BC857CW
BC847T	SOT416	SC-75	-	BC857T
BC847AT				BC857AT
BC847AT/DG				-
BC847BT				BC857BT
BC847CT				BC857CT
BC847AM	SOT883	SC-101	-	BC857AM
BC847BM				BC857BM
BC847CM				BC857CM
BC547 <sup>[2]</sup>	SOT54	SC-43A	TO-92	BC557 <sup>[2]</sup>
BC547B <sup>[2]</sup>				BC557B <sup>[2]</sup>
BC547C <sup>[2]</sup>				BC557C <sup>[2]</sup>

[1] /DG: halogen-free

[2] Also available in SOT54A and SOT54 variant packages (see [Section 2](#)).

## 1.2 Features

- Low current
- Low voltage
- Three different gain selections

## 1.3 Applications

- General-purpose switching and amplification

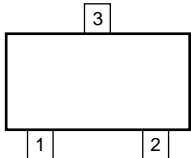
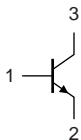
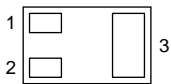
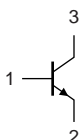
## 1.4 Quick reference data

**Table 2. Quick reference data**

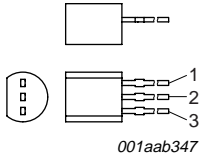
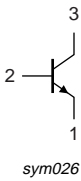
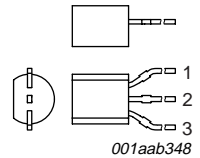
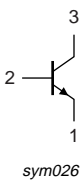
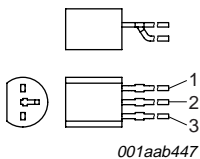
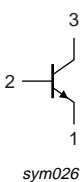
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CE0}$	collector-emitter voltage	open base	-	-	45	V
$I_C$	collector current		-	-	100	mA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	110	-	800	
	$h_{FE}$ group A		110	180	220	
	$h_{FE}$ group B		200	290	450	
	$h_{FE}$ group C		420	520	800	

## 2. Pinning information

**Table 3. Pinning**

Pin	Description	Simplified outline	Graphic symbol
<b>SOT23, SOT323, SOT416</b>			
1	base	 <p>006aaa144</p>	 <p>sym021</p>
2	emitter		
3	collector		
<b>SOT883</b>			
1	base	 <p>Transparent top view</p>	 <p>sym021</p>
2	emitter		
3	collector		

**Table 3. Pinning ...continued**

Pin	Description	Simplified outline	Graphic symbol
<b>SOT54</b>			
1	emitter	 <p>001aab347</p>	 <p>sym026</p>
2	base		
3	collector		
<b>SOT54A</b>			
1	emitter	 <p>001aab348</p>	 <p>sym026</p>
2	base		
3	collector		
<b>SOT54 variant</b>			
1	emitter	 <p>001aab447</p>	 <p>sym026</p>
2	base		
3	collector		

### 3. Ordering information

**Table 4. Ordering information**

Type number <sup>[1]</sup>	Package		Version
	Name	Description	
BC847	-	plastic surface-mounted package; 3 leads	SOT23
BC847A			
BC847B			
BC847B/DG			
BC847C			
BC847W	SC-70	plastic surface-mounted package; 3 leads	SOT323
BC847AW			
BC847BW			
BC847BW/DG			
BC847CW			

Table 4. Ordering information ...continued

Type number <sup>[1]</sup>	Package		
	Name	Description	Version
BC847T	SC-75	plastic surface-mounted package; 3 leads	SOT416
BC847AT			
BC847AT/DG			
BC847BT			
BC847CT			
BC847AM			
BC847BM			
BC847CM			
BC547 <sup>[2]</sup>	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BC547B <sup>[2]</sup>			
BC547C <sup>[2]</sup>			

[1] /DG: halogen-free

[2] Also available in SOT54 and SOT54 variant packages (see [Section 2](#) and [Section 9](#)).

## 4. Marking

Table 5. Marking codes

Type number <sup>[1]</sup>	Marking code <sup>[2]</sup>	Type number <sup>[1]</sup>	Marking code <sup>[2]</sup>
BC847	1H*	BC847AT	1E
BC847A	1E*	BC847AT/DG	B5
BC847B	1F*	BC847BT	1F
BC847B/DG	*BC	BC847CT	1G
BC847C	1G*	BC847AM	D4
BC847W	1H*	BC847BM	D5
BC847AW	1E*	BC847CM	D6
BC847BW	1F*	BC547	C547
BC847BW/DG	G9*	BC547B	C547B
BC847CW	1G*	BC547C	C547C
BC847T	1N	-	-

[1] /DG: halogen-free

[2] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

## 5. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	45	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
$I_C$	collector current		-	100	mA
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	200	mA
$I_{BM}$	peak base current	single pulse; $t_p \leq 1$ ms	-	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C			
	SOT23		[1] -	250	mW
	SOT323		[1] -	200	mW
	SOT416		[1] -	150	mW
	SOT883		[2][3] -	250	mW
	SOT54		[1] -	500	mW
$T_j$	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-65	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60 µm copper strip line, standard footprint.

## 6. Thermal characteristics

**Table 7. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT23		[1] -	-	500	K/W
	SOT323		[1] -	-	625	K/W
	SOT416		[1] -	-	833	K/W
	SOT883		[2][3] -	-	500	K/W
	SOT54		[1] -	-	250	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60 µm copper strip line, standard footprint.

## 7. Characteristics

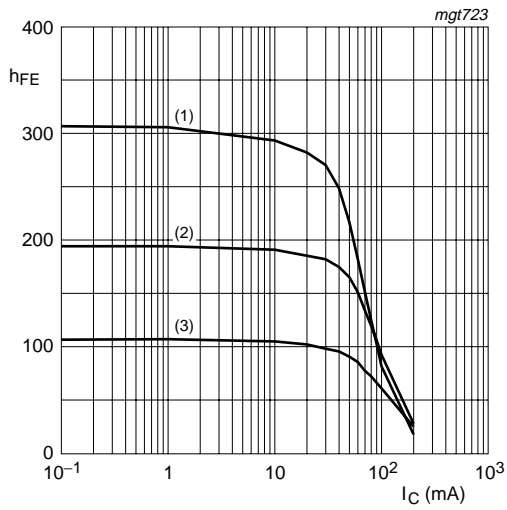
**Table 8. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	15	nA	
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	$\mu\text{A}$	
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA	
$h_{FE}$	DC current gain						
	$h_{FE}$ group A	$V_{CE} = 5\text{ V}; I_C = 10\text{ }\mu\text{A}$	-	90	-		
	$h_{FE}$ group B	$V_{CE} = 5\text{ V}; I_C = 10\text{ }\mu\text{A}$	-	150	-		
	$h_{FE}$ group C	$V_{CE} = 5\text{ V}; I_C = 10\text{ }\mu\text{A}$	-	270	-		
	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	110	-	800		
	$h_{FE}$ group A	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	110	180	220		
	$h_{FE}$ group B	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	200	290	450		
$h_{FE}$ group C	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	420	520	800			
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	90	200	mV	
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[1]	200	400	mV	
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	[2]	700	-	mV	
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[2]	900	-	mV	
$V_{BE}$	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	[2]	580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	-	-	770	mV	
$C_C$	collector capacitance	$I_E = I_C = 0\text{ A}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	-	-	1.5	pF	
$C_e$	emitter capacitance	$I_C = I_E = 0\text{ A}; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	-	11	-	pF	
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	-	-	MHz	
NF	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	-	2	10	dB	

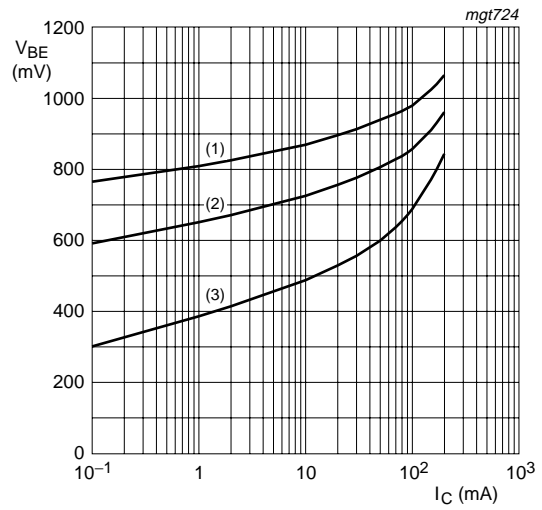
[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

[2]  $V_{BE}$  decreases by approximately 2 mV/K with increasing temperature.



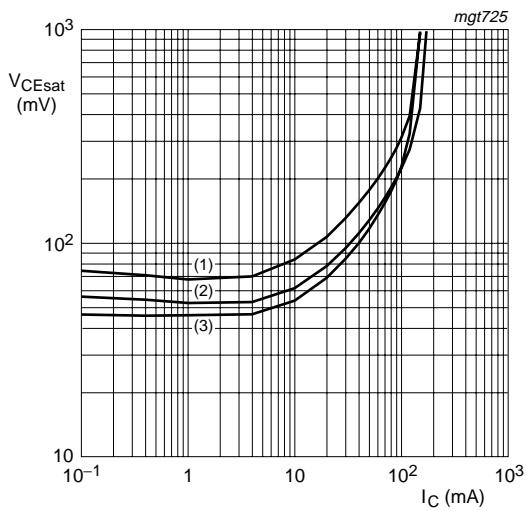
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 150\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 1. Selection A: DC current gain as a function of collector current; typical values**



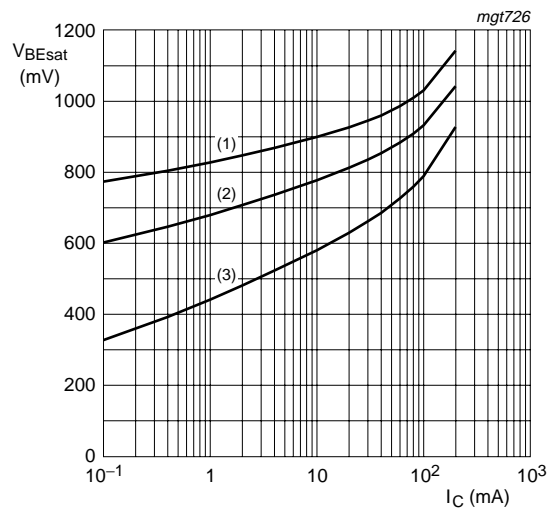
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 150\text{ °C}$

**Fig 2. Selection A: Base-emitter voltage as a function of collector current; typical values**



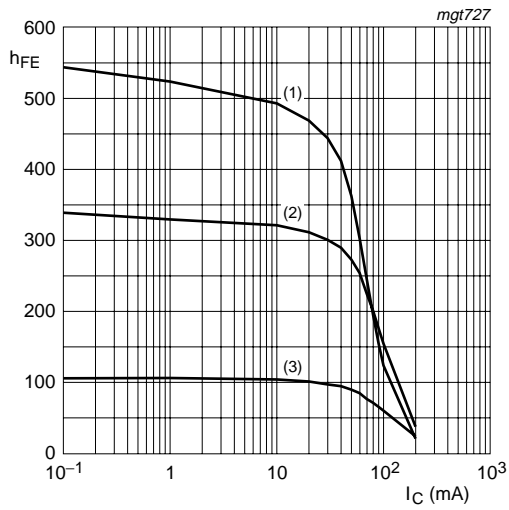
$I_C/I_B = 20$   
 (1)  $T_{amb} = 150\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 3. Selection A: Collector-emitter saturation voltage as a function of collector current; typical values**



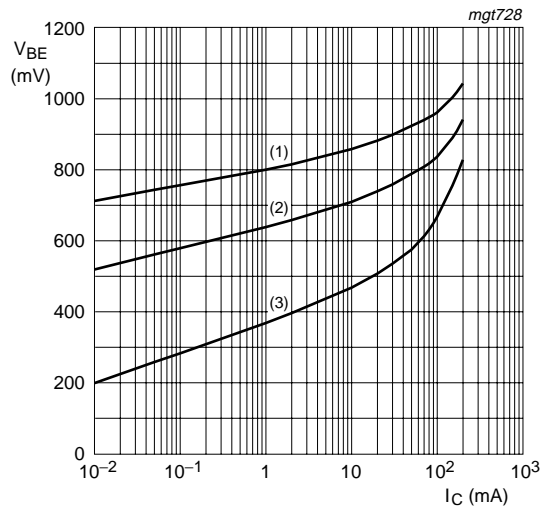
$I_C/I_B = 10$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 150\text{ °C}$

**Fig 4. Selection A: Base-emitter saturation voltage as a function of collector current; typical values**



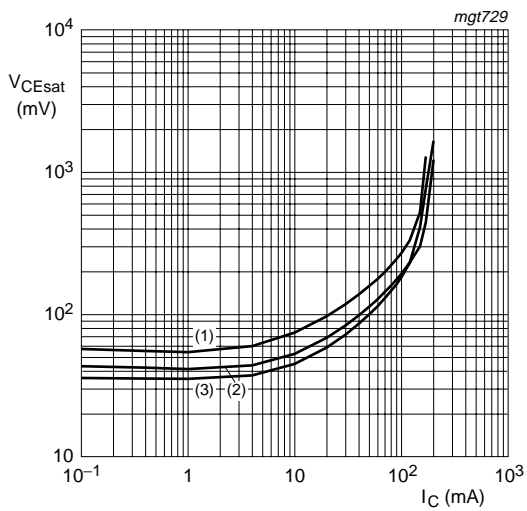
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 150\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 5. Selection B: DC current gain as a function of collector current; typical values**



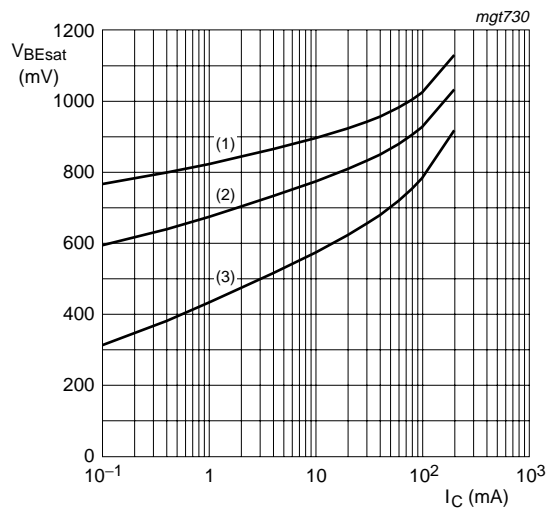
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 150\text{ °C}$

**Fig 6. Selection B: Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 150\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

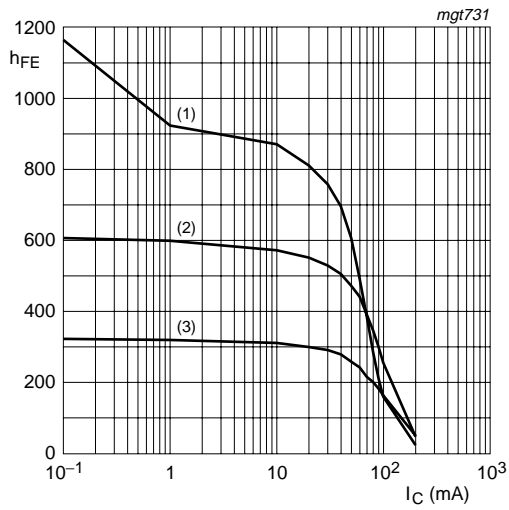
**Fig 7. Selection B: Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 10$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 150\text{ °C}$

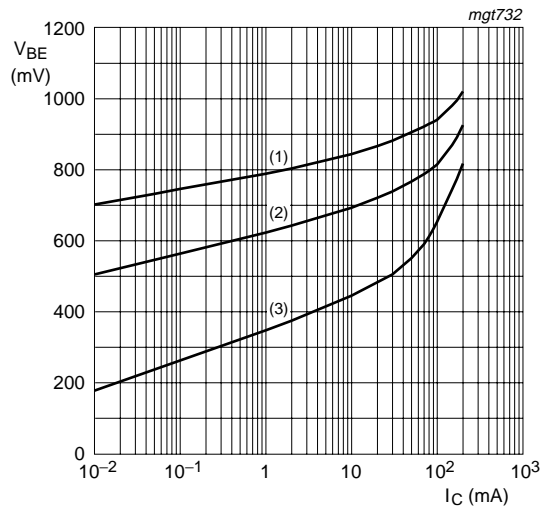
**Fig 8. Selection B: Base-emitter saturation voltage as a function of collector current; typical values**





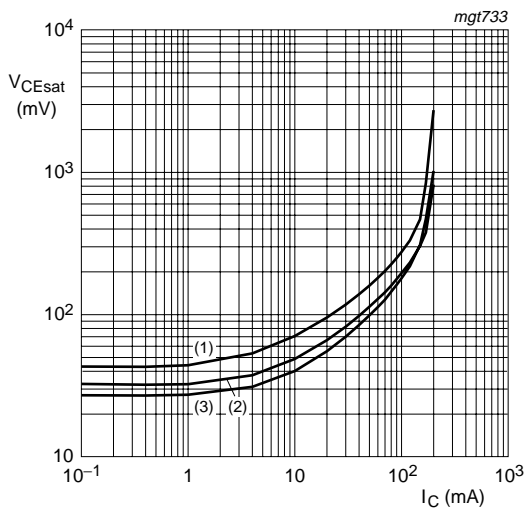
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = 150\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 9. Selection C: DC current gain as a function of collector current; typical values**



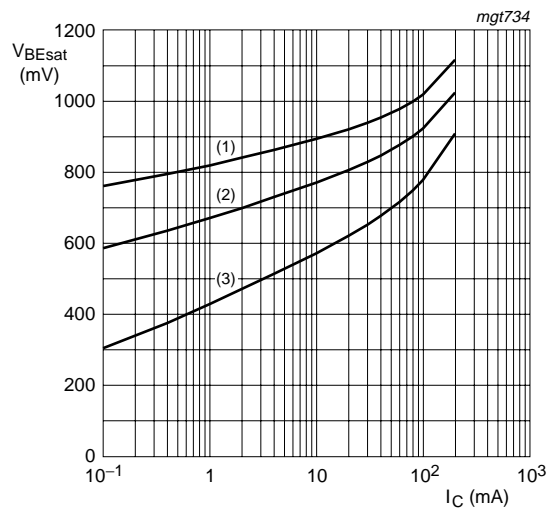
$V_{CE} = 5\text{ V}$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 150\text{ °C}$

**Fig 10. Selection C: Base-emitter voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 150\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

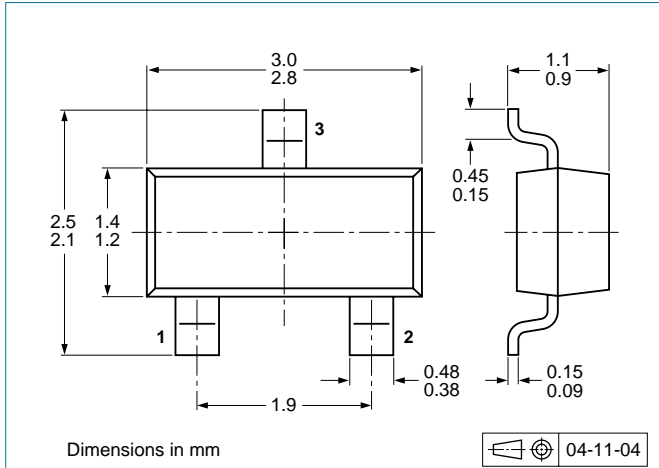
**Fig 11. Selection C: Collector-emitter saturation voltage as a function of collector current; typical values**



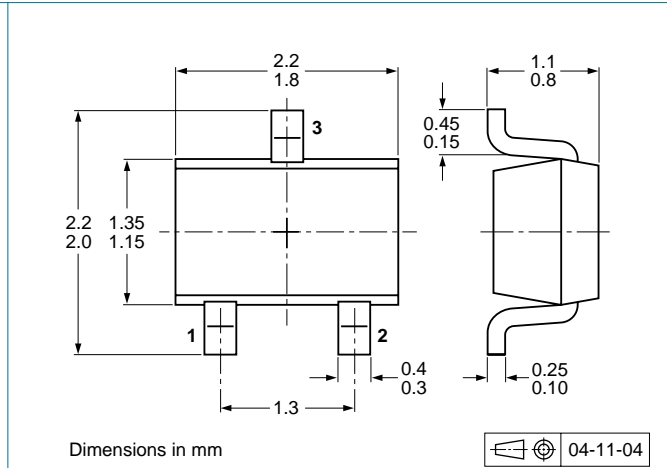
$I_C/I_B = 10$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 150\text{ °C}$

**Fig 12. Selection C: Base-emitter saturation voltage as a function of collector current; typical values**

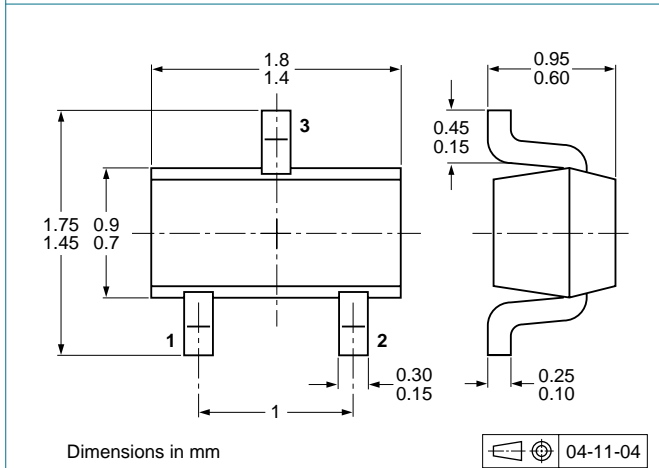
**8. Package outline**



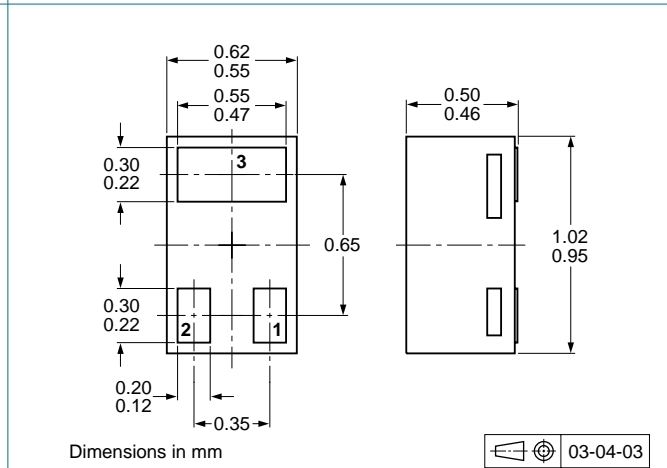
**Fig 13. Package outline SOT23 (TO-236AB)**



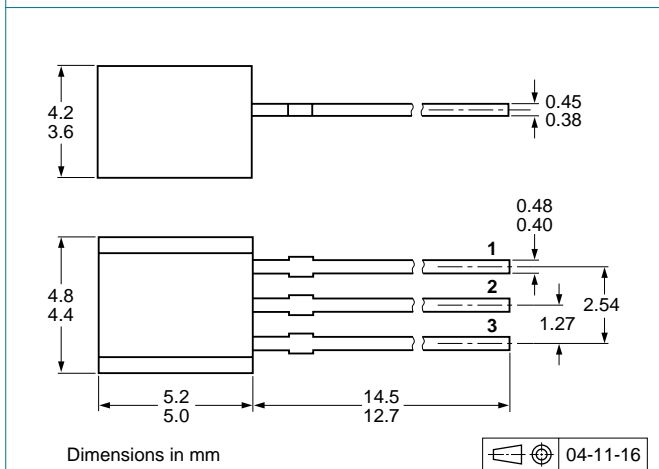
**Fig 14. Package outline SOT323 (SC-70)**



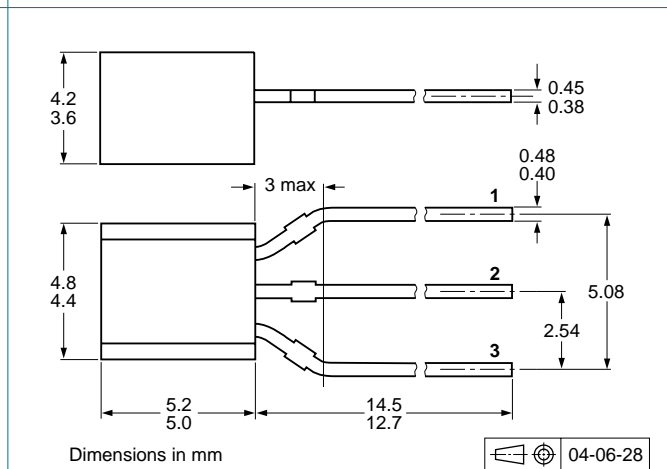
**Fig 15. Package outline SOT416 (SC-75)**



**Fig 16. Package outline SOT883 (SC-101)**



**Fig 17. Package outline SOT54 (SC-43A/TO-92)**



**Fig 18. Package outline SOT54A**

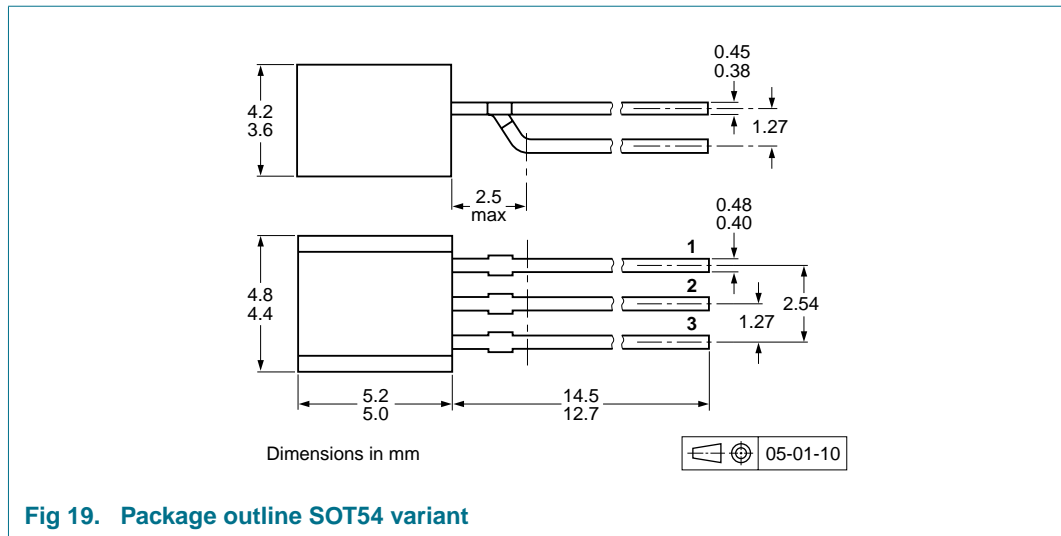


Fig 19. Package outline SOT54 variant

## 9. Packing information

**Table 9. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number <sup>[2]</sup>	Package	Description	Packing quantity		
			3000	5000	10000
BC847	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
BC847A					
BC847B					
BC847B/DG					
BC847C					
BC847W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135
BC847AW					
BC847BW					
BC847BW/DG					
BC847CW					
BC847T	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
BC847AT					
BC847AT/DG					
BC847BT					
BC847CT					
BC847AM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
BC847BM					
BC847CM					
BC547	SOT54	bulk, straight leads	-	-412	-
BC547B					
BC547C					

**Table 9. Packing methods ...continued**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number <sup>[2]</sup>	Package	Description	Packing quantity		
			3000	5000	10000
BC547 BC547B BC547C	SOT54A	tape and reel, wide pitch	-	-	-116
BC547 BC547B BC547C	SOT54A	tape ammopack, wide pitch	-	-	-126
BC547 BC547B BC547C	SOT54 variant	bulk, delta pinning	-	-112	-

[1] For further information and the availability of packing methods, see [Section 12](#).

[2] /DG: halogen-free

## 10. Revision history

**Table 10. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC847_BC547_SER_7	20081210	Product data sheet	-	BC847_BC547_SER_6
Modifications:				
				<ul style="list-style-type: none"> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li><a href="#">Table 1 "Product overview"</a>: enhanced</li> <li><a href="#">Table 4 "Ordering information"</a>: enhanced</li> <li><a href="#">Table 5 "Marking codes"</a>: enhanced</li> <li><a href="#">Table 6 "Limiting values"</a>: I<sub>EBO</sub> conditions amended</li> <li><a href="#">Table 8 "Characteristics"</a>: symbol N for parameter noise figure redefined to NF</li> <li><a href="#">Table 9 "Packing methods"</a>: enhanced</li> <li><a href="#">Section 11 "Legal information"</a>: updated</li> </ul>
BC847_BC547_SER_6	20050519	Product data sheet	-	BC846_BC847_BC848_5, BC847M_SERIES_2, BC846T_847T_SERIES_3, BC846W_BC847W_BC848W_4, BC546_547_4
BC846_BC847_BC848_5	20040206	Product specification	-	BC846_BC847_BC848_4
BC847M_SERIES_2	20040310	Product specification	-	BC847M_SERIES_1
BC846T_847T_SERIES_3	20001115	Product specification	-	BC846T_847T_2
BC846W_BC847W_ BC848W_4	20020204	Product specification	-	BC846W_847W_3
BC546_547_4	20041125	Product specification	-	BC546_547_3

## 11. Legal information

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Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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